



STGP7NC60HD

STGF7NC60HD - STGB7NC60HD

N-CHANNEL 14A - 600V - TO-220/TO-220FP/D²PAK

Very Fast PowerMESH™ IGBT

Table 1: General Features

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _C @ 100°C
STGP7NC60HD	600 V	< 2.5 V	14 A
STGF7NC60HD	600 V	< 2.5 V	6 A
STGB7NC60HD	600 V	< 2.5 V	14 A

- LOWER ON-VOLTAGE DROP (V_{cesat})
- OFF LOSSES INCLUDE TAIL CURRENT
- LOSSES INCLUDE DIODE RECOVERY ENERGY
- LOWER C_{RES}/C_{IES} RATIO
- HIGH FREQUENCY OPERATION UP TO 70 KHz
- VERY SOFT ULTRA FAST RECOVERY ANTI PARALLEL DIODE
- NEW GENERATION PRODUCTS WITH TIGHTER PARAMETER DISTRIBUTION

DESCRIPTION

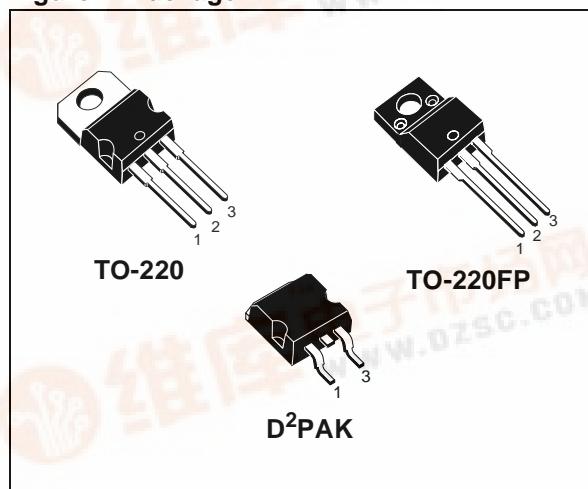
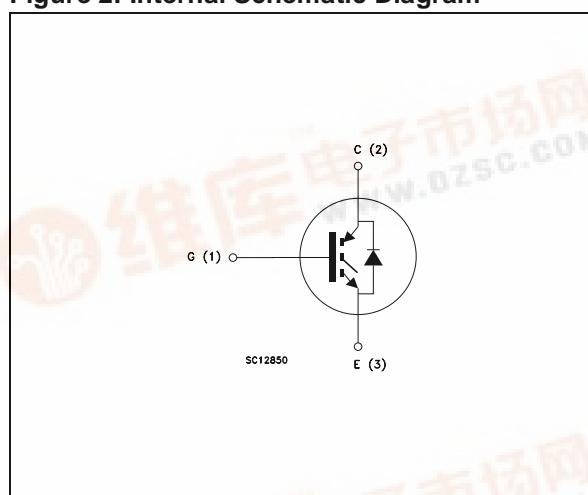
Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "H" identifies a family optimized for high frequency applications in order to achieve very high switching performances (reduced t_{fall}) maintaining a low voltage drop.

APPLICATIONS

- HIGH FREQUENCY INVERTERS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES
- MOTOR DRIVERS

Table 2: Order Code

PART NUMBER	MARKING	PACKAGE	PACKAGING
STGP7NC60HD	GP7NC60HD	TO-220	TUBE
STGF7NC60HD	GF7NC60HD	TO-220FP	TUBE
STGB7NC60HDT4	GB7NC60HD	D ² PAK	TAPE & REEL

Figure 1: Package**Figure 2: Internal Schematic Diagram**

STGP7NC60HD - STGF7NC60HD - STGB7NC60HD

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value		Unit
		STGP7NC60HD STGB7NC60HD	STGF7NC60HD	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600		V
V _{ECR}	Emitter-Collector Voltage	20		V
V _{GE}	Gate-Emitter Voltage	±20		V
I _C	Collector Current (continuous) at T _C = 25°C (#)	25	10	A
I _C	Collector Current (continuous) at T _C = 100°C (#)	14	6	A
I _{CM} (✉)	Collector Current (pulsed)	50		A
I _F	Diode RMS Forward Current at T _C = 25°C	20		A
P _{TOT}	Total Dissipation at T _C = 25°C	80	25	W
	Derating Factor	0.64	0.20	W/°C
V _{ISO}	Insulation Withstand Voltage A.C.(t = 1 sec; T _c = 25°C)	--	2500	V
T _{stg}	Storage Temperature	– 55 to 150		°C
T _j	Operating Junction Temperature			°C

(✉) Pulse width limited by max. junction temperature.

Table 4: Thermal Data

			Min.	Typ.	Max.	
R _{thj-case}	Thermal Resistance Junction-case	TO-220 D ² PAK			1.56	°C/W
		TO-220FP			5.0	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient				62.5	°C/W
T _L	Maximum Lead Temperature for Soldering Purpose (1.6 mm from case, for 10 sec.)			300		°C

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

Table 5: Main Parameters

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collector-Emitter Breakdown Voltage	I _C = 1 mA, V _{GE} = 0	600			V
I _{CES}	Collector cut-off Current (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25 °C V _{CE} = Max Rating, T _C = 125 °C			10 1	μA mA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20V , V _{CE} = 0			±100	nA
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250 μA	3.75		5.75	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} = 15V, I _C = 7 A V _{GE} = 15V, I _C = 7 A, T _c = 125°C		1.85 1.7	2.5	V

(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

STGP7NC60HD - STGF7NC60HD - STGB7NC60HD

ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 6: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{CE} = 15 \text{ V}$, $I_C = 7 \text{ A}$		4.30		S
C_{ies}	Input Capacitance	$V_{CE} = 25 \text{ V}$, $f = 1 \text{ MHz}$, $V_{GE} = 0$		720		pF
C_{oes}	Output Capacitance			81		pF
C_{res}	Reverse Transfer Capacitance			17		pF
Q_g	Total Gate Charge	$V_{CE} = 390 \text{ V}$, $I_C = 7 \text{ A}$,		35		nC
Q_{ge}	Gate-Emitter Charge	$V_{GE} = 15 \text{ V}$		7		nC
Q_{gc}	Gate-Collector Charge	(see Figure 22)		16		nC
I_{CL}	Turn-Off SOA Minimum Current	$V_{clamp} = 480 \text{ V}$, $T_j = 150^\circ\text{C}$ $R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$	50			A

(1) Pulsed: Pulse duration= 300 μs , duty cycle 1.5%

Table 7: Switching On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 390 \text{ V}$, $I_C = 7 \text{ A}$		18.5		ns
t_r	Current Rise Time	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_j = 25^\circ\text{C}$		8.5		ns
$(di/dt)_{on}$	Turn-on Current Slope	(see Figure 19)		1060		A/ μs
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 390 \text{ V}$, $I_C = 7 \text{ A}$		18.5		ns
t_r	Current Rise Time	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_j = 125^\circ\text{C}$		7		ns
$(di/dt)_{on}$	Turn-on Current Slope	(see Figure 20)		1000		A/ μs

Table 8: Switching Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off Voltage Rise Time	$V_{CC} = 390 \text{ V}$, $I_C = 7 \text{ A}$		27		ns
$t_d(off)$	Turn-off Delay Time	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$		72		ns
t_f	Current Fall Time	$T_j = 25^\circ\text{C}$ (see Figure 20)		60		ns
$t_r(V_{off})$	Off Voltage Rise Time	$V_{CC} = 390 \text{ V}$, $I_C = 7 \text{ A}$		56		ns
$t_d(off)$	Turn-off Delay Time	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$		116		ns
t_f	Current Fall Time	$T_j = 125^\circ\text{C}$ (see Figure 20)		105		ns

Table 9: Switching Energy

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
E_{on} (2)	Turn-on Switching Losses	$V_{CC} = 390 \text{ V}$, $I_C = 7 \text{ A}$		95		μJ
E_{off} (3)	Turn-off Switching Loss	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_j = 25^\circ\text{C}$		115		μJ
E_{ts}	Total Switching Loss	(see Figure 19)		210		μJ
E_{on} (2)	Turn-on Switching Losses	$V_{CC} = 390 \text{ V}$, $I_C = 7 \text{ A}$		140		μJ
E_{off} (3)	Turn-off Switching Loss	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_j = 125^\circ\text{C}$		215		μJ
E_{ts}	Total Switching Loss	(see Figure 20)		355		μJ

(2) E_{on} is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs & DIODE are at the same temperature (25°C and 125°C)

(3) Turn-off losses include also the tail of the collector current.

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Table 10: Collector-Emitter Diode

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_f	Forward On-Voltage	$I_f = 3.5 \text{ A}$ $I_f = 3.5 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$		1.3 1.1	1.9	V V
t_{rr}	Reverse Recovery Time	$I_f = 7 \text{ A}, V_R = 40 \text{ V},$ $T_j = 25 \text{ }^\circ\text{C}, di/dt = 100 \text{ A}/\mu\text{s}$	37 22 40 2.1 0.68			ns ns nC A
t_a	Reverse Recovery Charge					
Q_{rr}	Reverse Recovery Current					
I_{rrm}	Softness factor of the diode					
S						
t_{rr}	Reverse Recovery Time	$I_f = 7 \text{ A}, V_R = 40 \text{ V},$ $T_j = 125 \text{ }^\circ\text{C}, di/dt = 100 \text{ A}/\mu\text{s}$	61 34 98 3.2 0.79			ns ns nC A
t_a	Reverse Recovery Charge					
Q_{rr}	Reverse Recovery Current					
I_{rrm}	Softness factor of the diode					
S						

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Figure 3: Output Characteristics

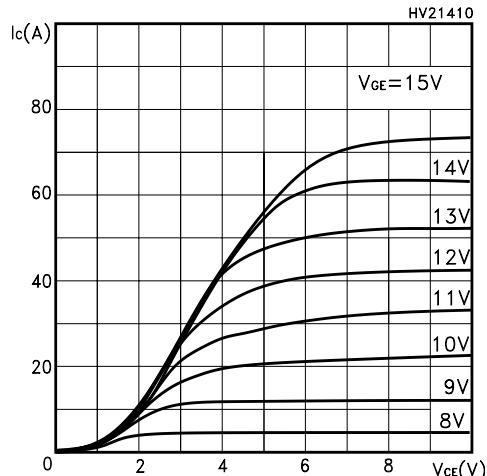


Figure 4: Transconductance

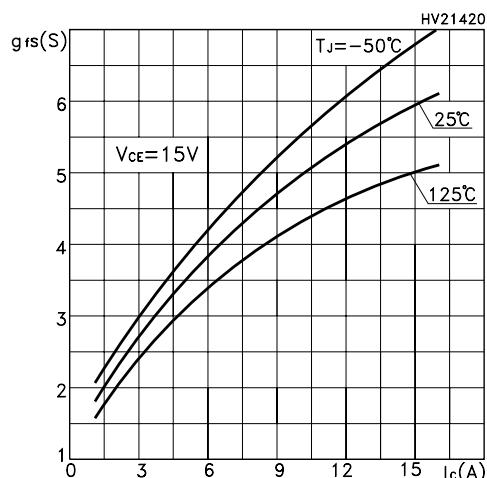


Figure 5: Collector-Emitter On Voltage vs Collector Current

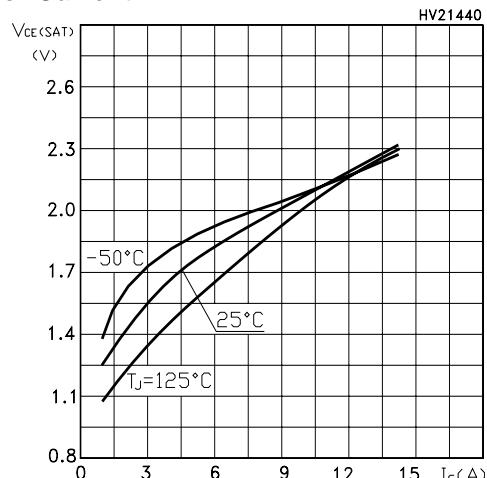


Figure 6: Transfer Characteristics

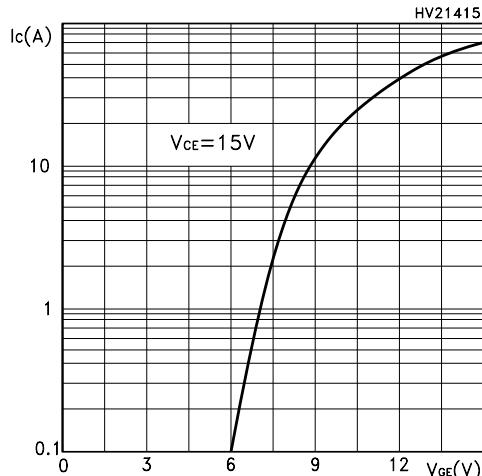


Figure 7: Collector-Emitter On Voltage vs Temperature

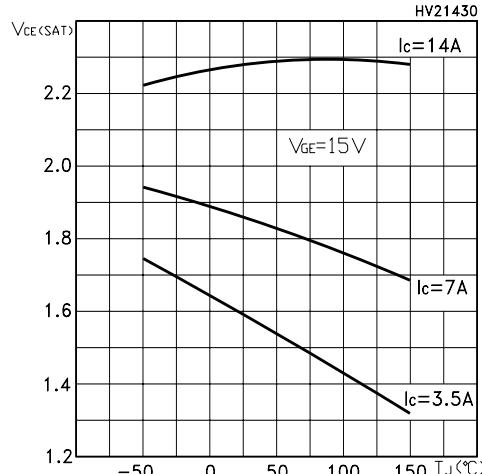
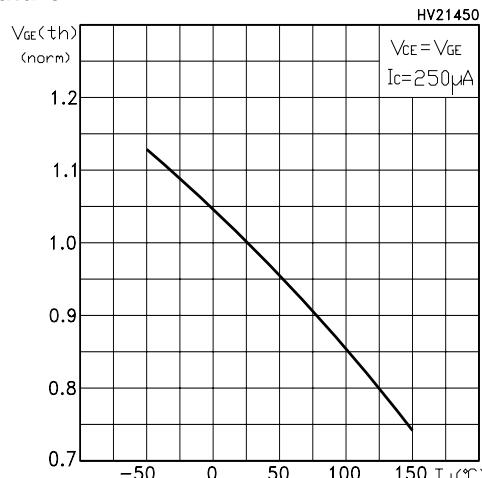


Figure 8: Normalized Gate Threshold vs Temperature



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Figure 9: Normalized Breakdown Voltage vs Temperature

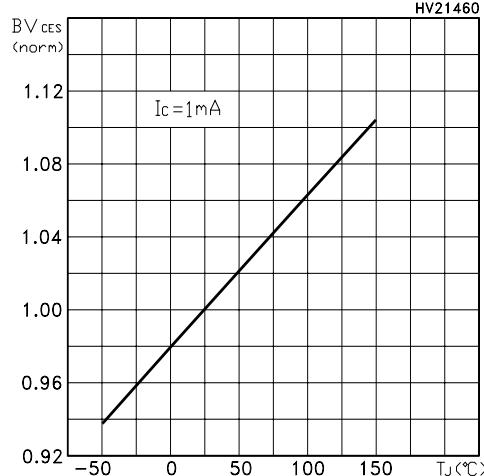


Figure 10: Capacitance Variations

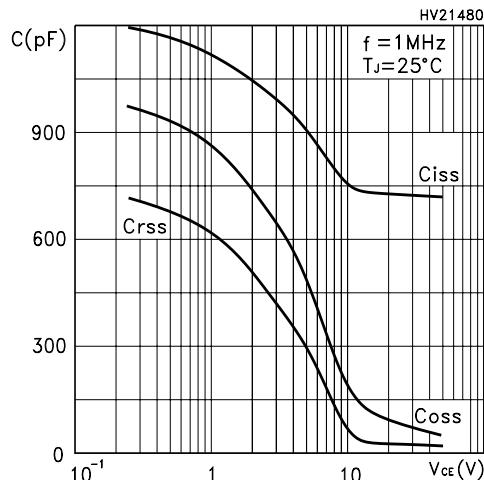


Figure 11: Total Switching Losses vs Gate Resistance

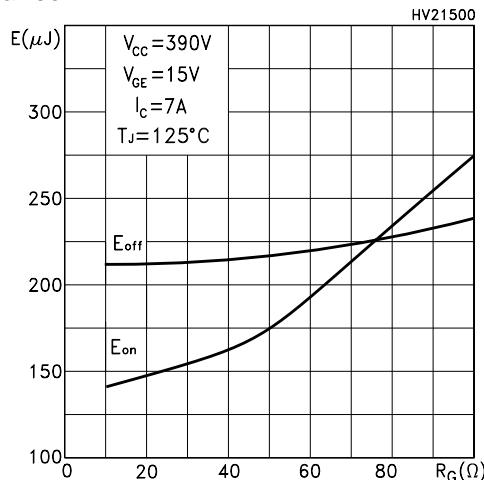


Figure 12: Gate Charge vs Gate-Emitter Voltage

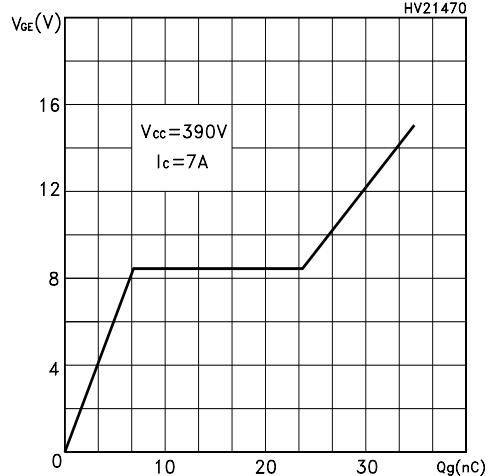


Figure 13: Total Switching Losses vs Temperature

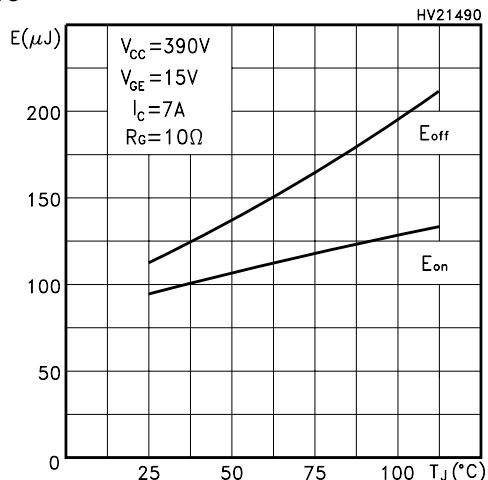
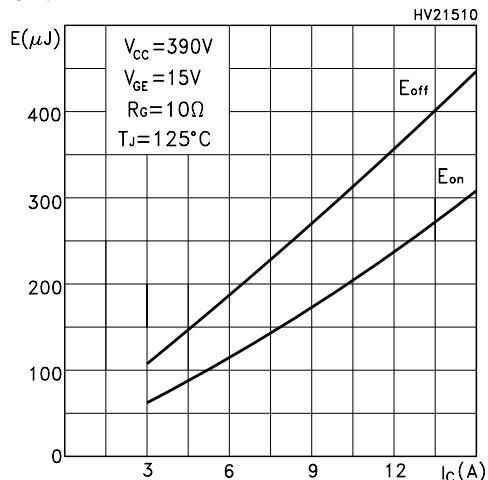


Figure 14: Total Switching Losses vs Collector Current



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Figure 15: Thermal Impedance For TO-220/ D²PAK

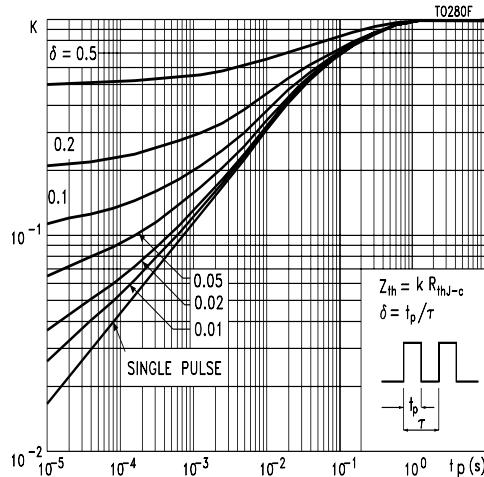


Figure 16: Thermal Impedance For TO-220FP

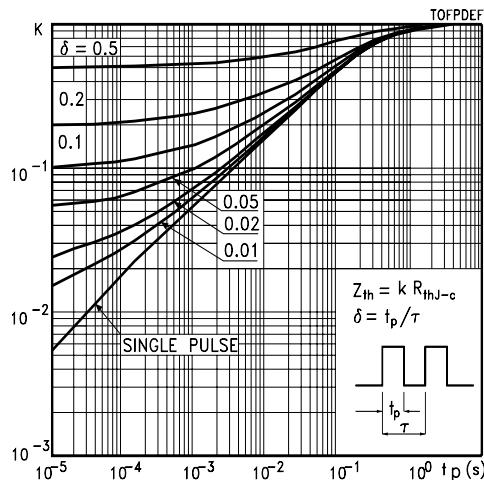


Figure 17: Turn-Off SOA

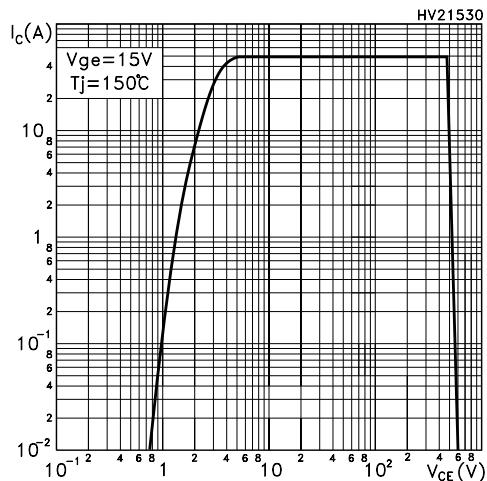
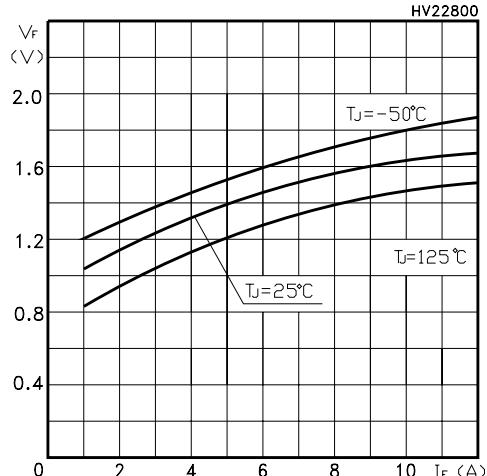
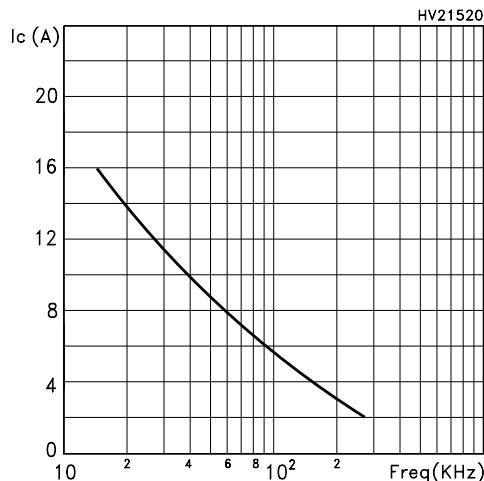


Figure 18: Emitter-Collector Diode Characteristics



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Figure 19: Ic vs Frequency



For a fast IGBT suitable for high frequency applications, the typical collector current vs. maximum operating frequency curve is reported. That frequency is defined as follows:

$$f_{MAX} = (P_D - P_C) / (E_{ON} + E_{OFF})$$

- 1) The maximum power dissipation is limited by maximum junction to case thermal resistance:

$$P_D = \Delta T / R_{THJ-C}$$

considering $\Delta T = T_J - T_C = 125^\circ\text{C} - 75^\circ\text{C} = 50^\circ\text{C}$

- 2) The conduction losses are:

$$P_C = I_C * V_{CE(SAT)} * \delta$$

with 50% of duty cycle, V_{CESAT} typical value @ 125°C.

- 3) Power dissipation during ON & OFF commutations is due to the switching frequency:

$$P_{SW} = (E_{ON} + E_{OFF}) * freq.$$

- 4) Typical values @ 125°C for switching losses are used (test conditions: $V_{CE} = 390\text{V}$, $V_{GE} = 15\text{V}$, $R_G = 3.3\text{ Ohm}$). Furthermore, diode recovery energy is included in the E_{ON} (see note 2), while the tail of the collector current is included in the E_{OFF} measurements (see note 3).

STGP7NC60HD - STGF7NC60HD - STGB7NC60HD

Figure 20: Test Circuit for Inductive Load Switching

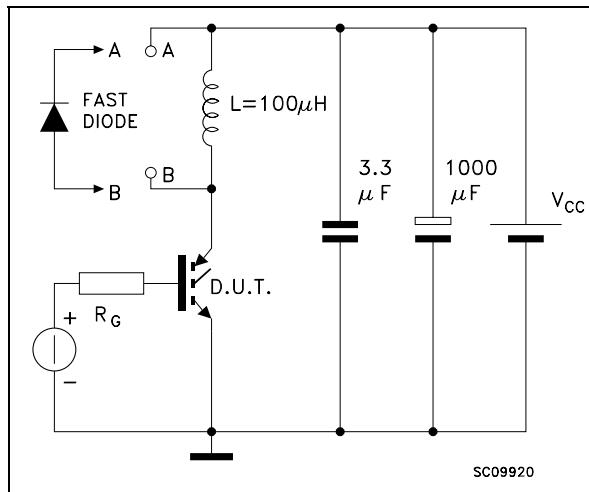


Figure 21: Switching Waveforms

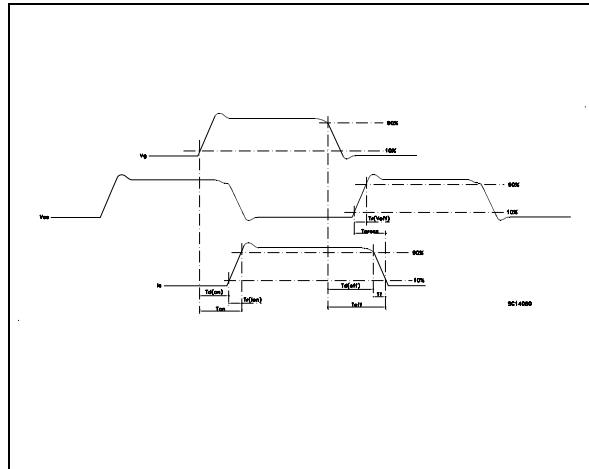


Figure 22: Gate Charge Test Circuit

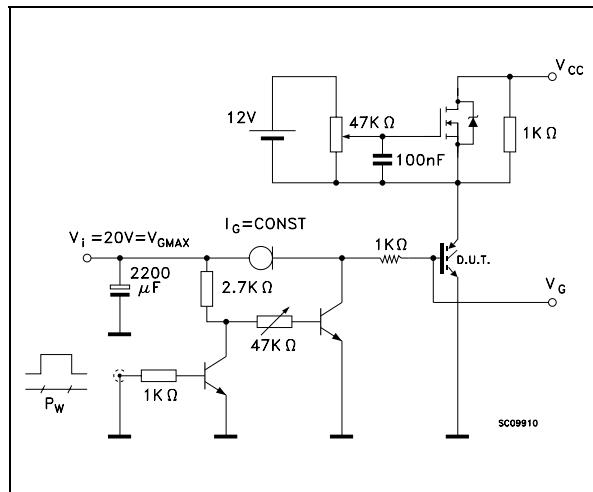
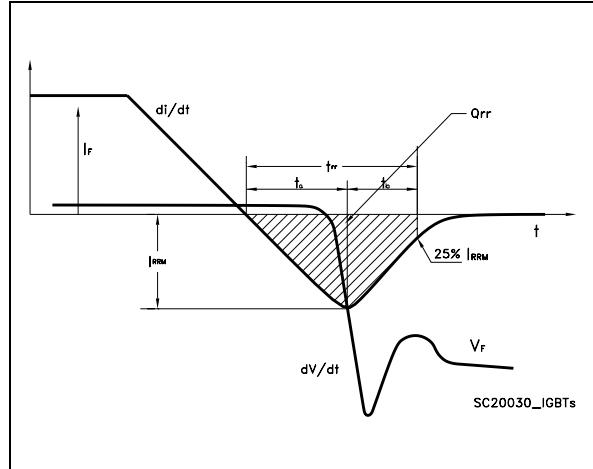


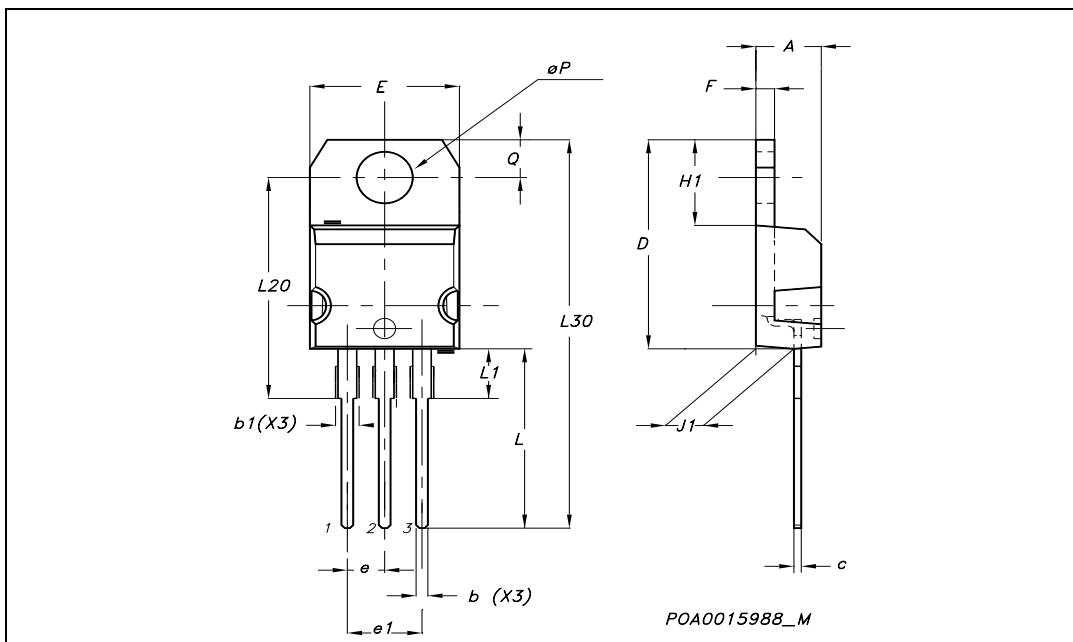
Figure 23: Diode Recovery Time Waveforms



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TO-220 MECHANICAL DATA

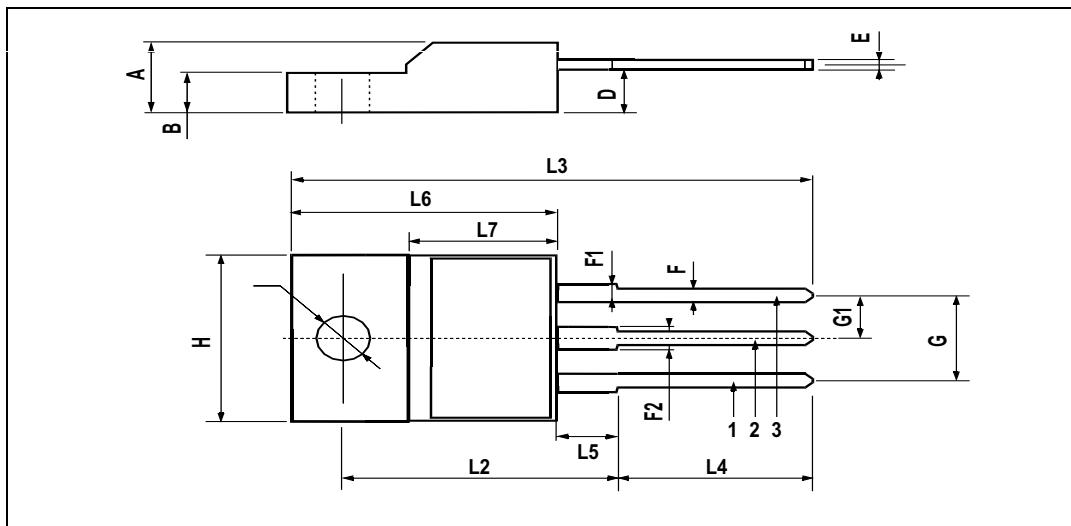
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ϕP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



STGP7NC60HD - STGF7NC60HD - STGB7NC60HD

TO-220FP MECHANICAL DATA

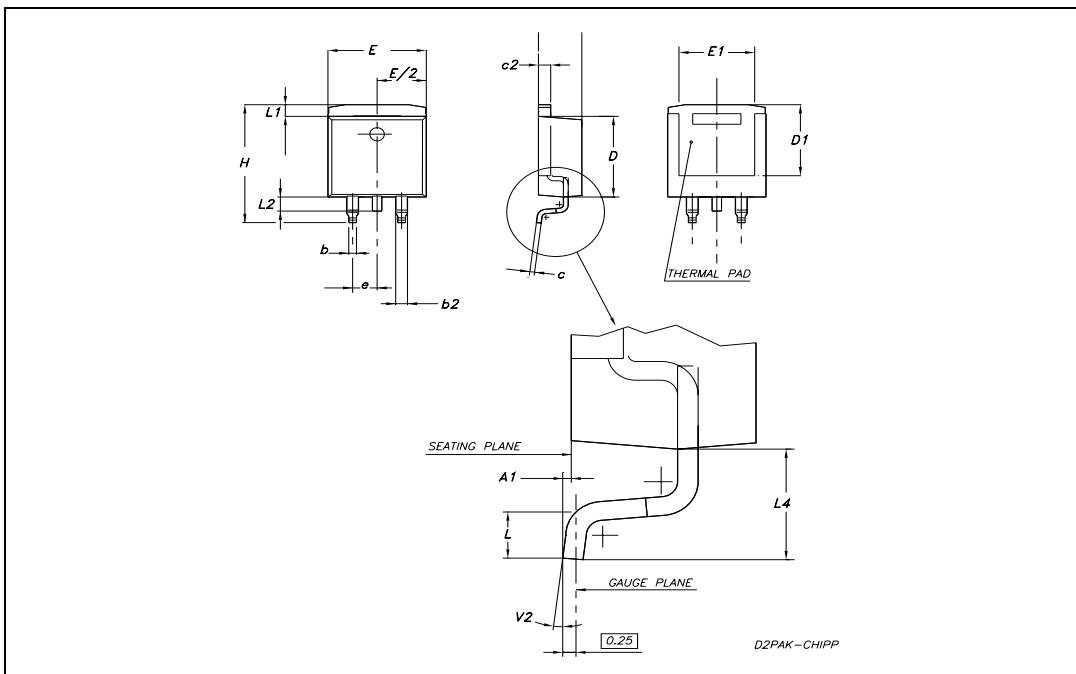
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



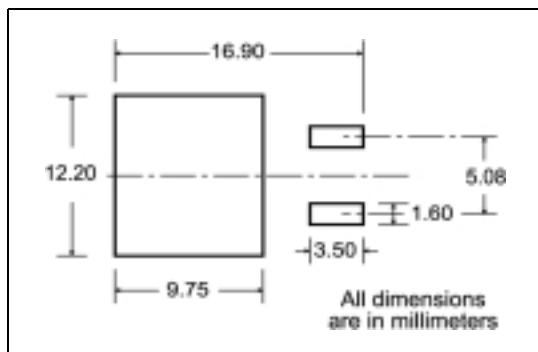
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TO-263 (D²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.57	0.178		0.180
A1	0.00		0.25	0.00		0.009
b	0.71		0.91	0.028		0.350
b2	1.15		1.40	0.045		0.055
c	0.46		0.61	0.018		0.024
c2	1.22		1.40	0.048		0.055
D	8.89	9.02	9.40	0.350	0.355	0.370
D1	8.01			0.315		
E	10.04		10.28	0.395		0.404
e		2.54			0.010	
H	13.10		13.70	0.515		0.540
L	1.30		1.70	0.051		0.067
L1	1.15		1.39	0.045		0.054
L2	1.27		1.77	0.050		0.069
L4	2.70		3.10	0.106		0.122
V2	0°		8°	0°		8°



D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

TAPE MECHANICAL DATA					REEL MECHANICAL DATA				
DIM.	mm		inch		DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.		MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421	A		330		12.992
B0	15.7	15.9	0.618	0.626	B	1.5		0.059	
D	1.5	1.6	0.059	0.063	C	12.8	13.2	0.504	0.520
D1	1.59	1.61	0.062	0.063	D	20.2		0.795	
E	1.65	1.85	0.065	0.073	G	24.4	26.4	0.960	1.039
F	11.4	11.6	0.449	0.456	N	100		3.937	
K0	4.8	5.0	0.189	0.197	T		30.4		1.197
P0	3.9	4.1	0.153	0.161					
P1	11.9	12.1	0.468	0.476					
P2	1.9	2.1	0.075	0.082					
R	50		1.574						
T	0.25	0.35	0.0098	0.0137					
W	23.7	24.3	0.933	0.956					

TAPE MECHANICAL DATA

Diagram illustrating tape slot dimensions and access hole location. The slot is 25mm min. width and 40mm min. access hole at slot location. The slot is in cone for tape start. Full radius is indicated.

REEL MECHANICAL DATA

Diagram illustrating reel dimensions and base/bulk quantities. Dimensions include A (330 mm), B (1.5 mm), C (12.8 mm), D (20.2 mm), G (24.4 mm), N (100 mm), and T (30.4 mm). Base quantity is 1000 and Bulk quantity is 1000.

TAPE Schematic

Diagram showing the tape structure with 10 pitches cumulative tolerance on tape +/- 0.2 mm. It indicates the top cover tape, center line of cavity, user direction of feed, and bending radius R min. The tape is labeled TRL and FEED DIRECTION.

* on sales type

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Table 11: Revision History 9

Date	Revision	Description of Changes
07-Jun-2004	4	Stylesheet update. No content change
19-Aug-2004	5	Complete Version
17-Sep-2004	6	Figure 18 has been added
09-Nov-2004	7	Final datasheet
19-Jan-2005	8	Datasheet updated
09-Jun-2005	9	Modified title

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